

BL940-1100-01 High Power type Top LED with Lens

BL940-1100-01 is an GaAs LED mounted on copper heat sink and molded with epoxy lens.

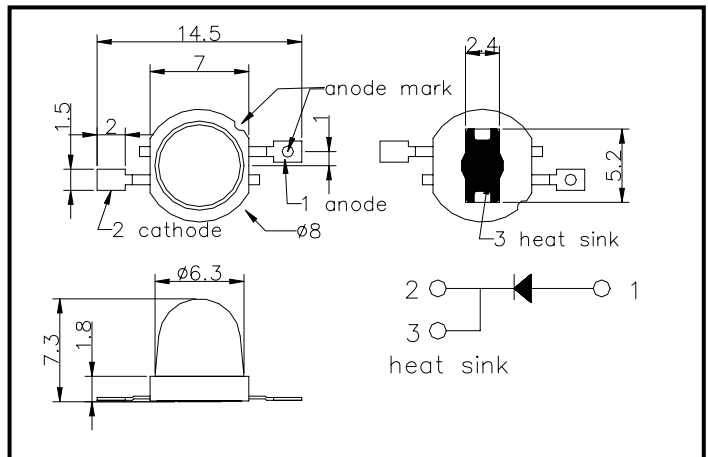
On forward bias, it emits a band of radiation which peaks 940nm.

These devices are able to be operated at pulsed current of 4A under 2.6V for stable long life.

◆ Specifications

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|---------------------|----------------------|
| 1) Product Name | Super Flux type LED |
| 2) Type No. | BL940-1100-01 |
| 3) Chip | |
| (1) Chip Material | GaAs |
| (2) Chip Dimension | 1000um*1000um |
| (3) Peak Wavelength | 940nm typ. |
| 4) Package | |
| (1) Type | Super Beam type LED |
| (2) Resin Material | Epoxy Resin |
| (3) Lead Frame | Silver Plated Copper |

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	900	mW	T _a =25°C
Forward Current	I _F	600	mA	T _a =25°C
Pulse Forward Current	I _{FP}	4000	mA	T _a =25°C
Reverse Voltage	V _R	10	V	T _a =25°C
Operating Temperature	T _{OPR}	-30 ~ +85	°C	
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	265	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 265°C

◆ Electro-Optical Characteristics [T_a=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =200mA		1.25	1.5	V
Pulsed Forward Voltage	V _F	I _{FP} =4A		2.6	3.5	V
Reverse Current	I _R	V _R =10V			10	uA
Total Radiated Power	P _O	I _F =200mA	25.0	45.0		mW
Radiant Intensity	I _E	I _F =200mA		90		mW/sr
Peak Wavelength	λ _P	I _F =50mA		940		nm
Half Width	Δλ	I _F =50mA		60		nm
Viewing Half Angle	θ _{1/2}	I _F =50mA		± 7		deg.
Rise Time	t _r	I _F =50mA		1000		ns
Fall Time	t _f	I _F =50mA		500		ns

‡Total Radiated Power is measured by Photodyne #500

‡Radiant Intensity is measured by Tektronix J-6512.